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Part Number	Customer				
Category	Parameter		Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	WaferVendor	
	2.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor	
	3.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor	
	4.0	Growth Method	CZ	Wafer Vendor	
	5.0	Туре	Any	Wafer Vendor	
	6.0	Dopant	Any	Wafer Vendor	
	7.0	Resistivity	0.1~ 100 ohm cm	Wafer Vendor	
	8.0	Overall Thickness	380.00 +/- 10.00 um	Wafer Vendor	
	9.0	Total Thickness Variation (TTV)	<3.00um	Guaranteed by process	
	10.0	Bow	<50.00um	ADE to ASTM F534, 20%	
	11.0	Warp	<50.00um	ADE to ASTM F657, 20%	
	12.0	Lasermarking	On wafer FRONTSIDE opposite the flat. Scribe format: [ICE-6-380.XXXX] (unique scribe)	Guaranteed by process	
	13.0	Orientation	<100> +/-0.5	Wafer Vendor	
	14.0	Back Surface Quality	Polished.	Wafer Vendor	
	15.0	Front Surface Quality	Prime	Wafer Vendor	
	16.0	Edge Chips	None	Bright Light 100% (note 2)	
HandleSilicon	17.0	Handle Thickness	380.00 +/- 10.00 um	ADE	
	18.0	Surface Haze	None	Bright Light, 100% (note 2).	
	19.0	Total scratch length	None	Bright Light, 100% (note 2).	

Icemos Technology Ltd

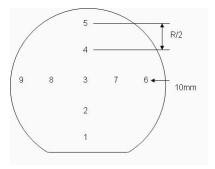
Product Specification

1003.291601

Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box :	Max 25		
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspect	tion performed using microscope scan as below. 5x objective.		

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information